



Wireless Components

ASK Single Conversion Receiver

TDA 5200 Version 2.7

Specification March 2000

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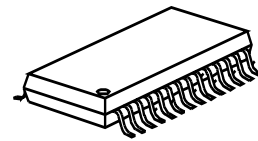
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Product Info

General Description

The IC is a very low power consumption single chip ASK Single Conversion Receiver for the frequency bands 868-870 MHz and 433-435 MHz. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

Package



Features

- Low supply current ($I_s = 4.8\text{mA typ. at } 868\text{MHz}$, $I_s = 4.6\text{mA typ. at } 434\text{MHz}$)
- Supply voltage range $5\text{V} \pm 10\%$
- Power down mode with very low supply current (50nA typ)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity $< -107\text{dBm}$
- Selectable frequency ranges 868-870 MHz and 433-435 MHz
- Limiter with RSSI generation, operating at 10.7MHz
- Selectable reference frequency
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold

Application

- Keyless Entry Systems
- Remote Control Systems
- Alarm Systems
- Low Bitrate Communication Systems

Ordering Information

Type	Ordering Code	Package
TDA 5200	Q67037-A1049	P-TSSOP-28-1
available on tape and reel		

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Product Description

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2.1 Overview

The IC is a very low power consumption single chip ASK Single Conversion Receiver for the frequency bands 868-870 MHz and 433-435 MHz. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

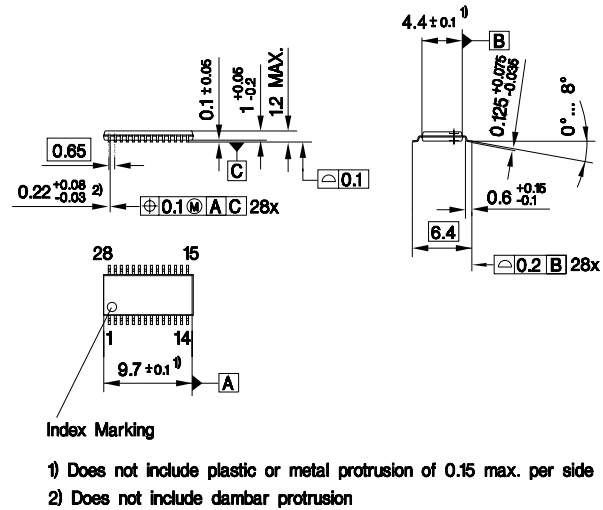
2.2 Application

- Keyless Entry Systems
- Remote Control Systems
- Alarm Systems
- Low Bitrate Communication Systems

2.3 Features

- Low supply current ($I_s = 4.8 \text{ mA typ. at } 868\text{MHz}, 4.6\text{mA typ. at } 434\text{MHz}$)
- Supply voltage range $5\text{V} \pm 10\%$
- Power down mode with very low supply current (100nA max.)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity $< -107\text{dBm}$
- Selectable frequency ranges 868-870 MHz and 433-435 MHz
- Selectable reference frequency
- Limiter with RSSI generation, operating at 10.7MHz
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold

2.4 Package Outlines



P_TSSOP_28.EPS

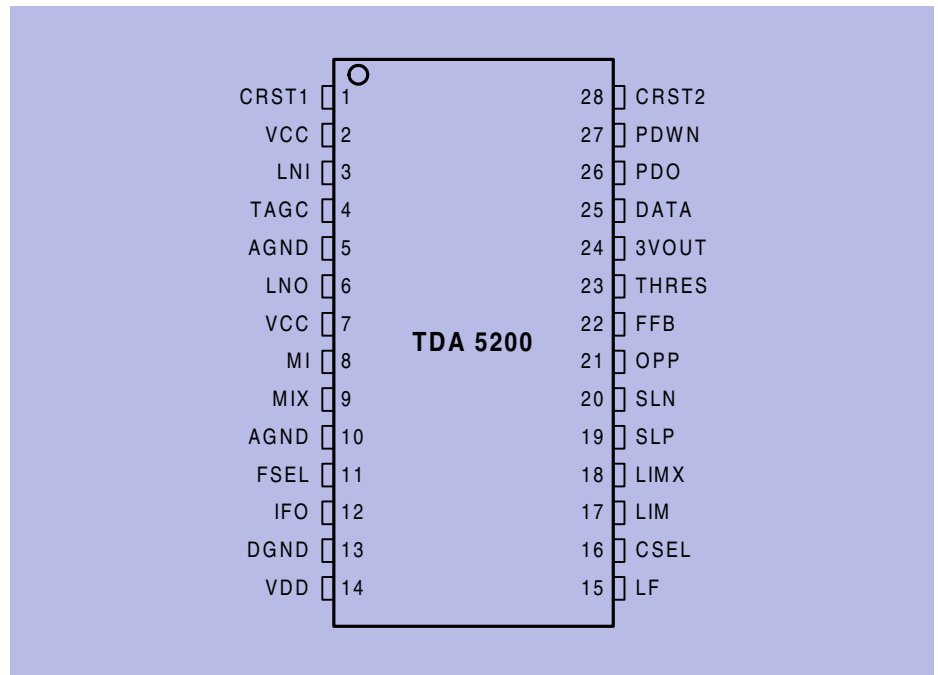
Figure 2-1 P-TSSOP-28-1 package outlines

3 Functional Description

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3.1 Pin Configuration

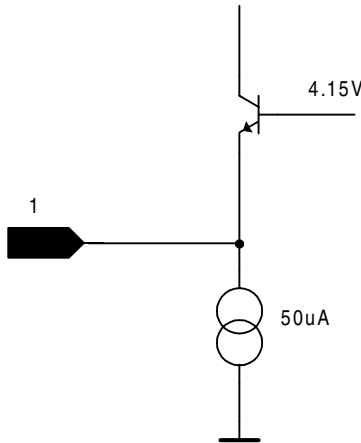
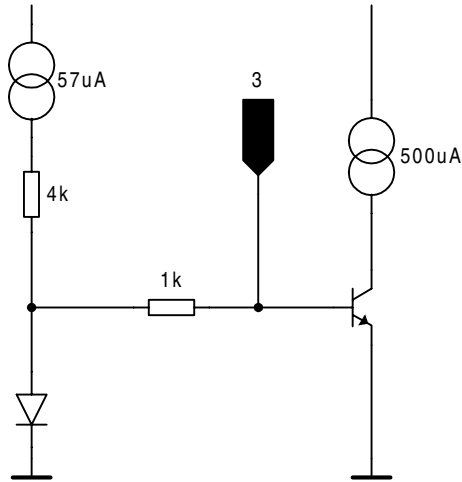


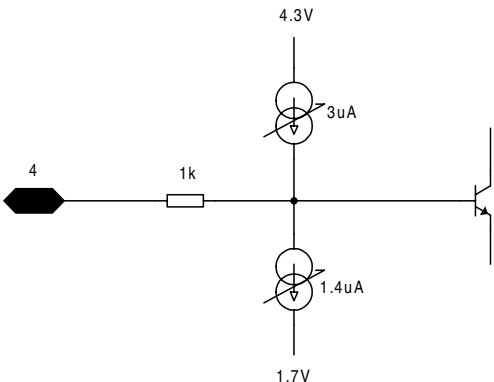
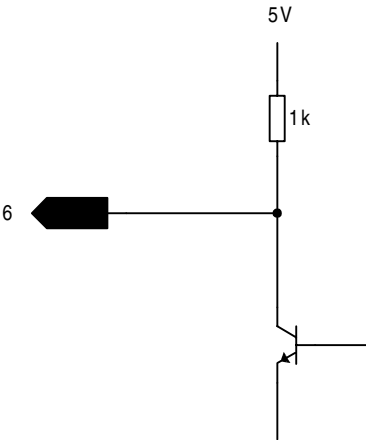
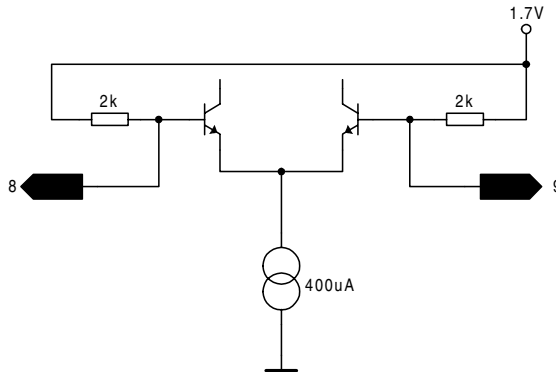
Pin_Configuration.wmf

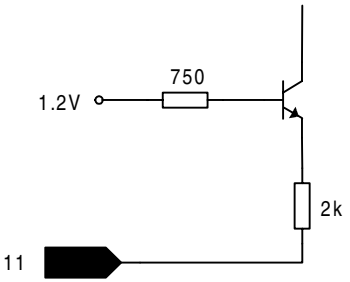
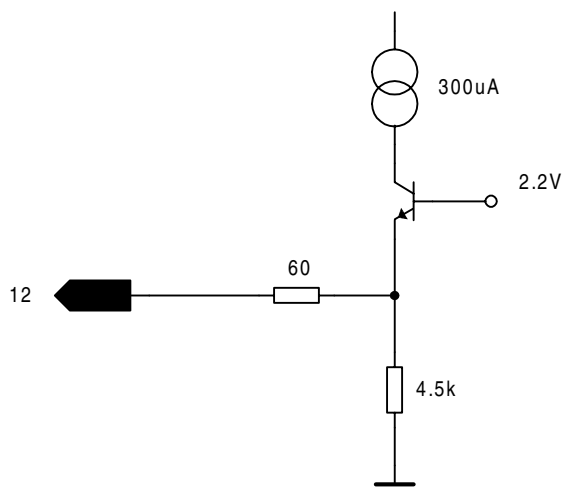
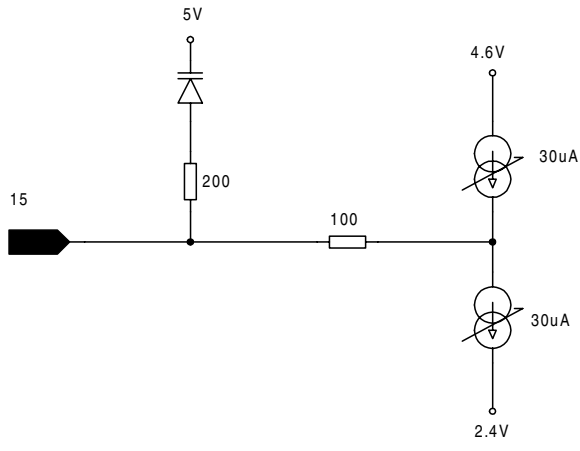
Figure 3-1 IC Pin Configuration

3.2 Pin Definition and Function

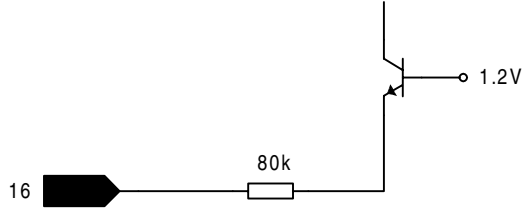
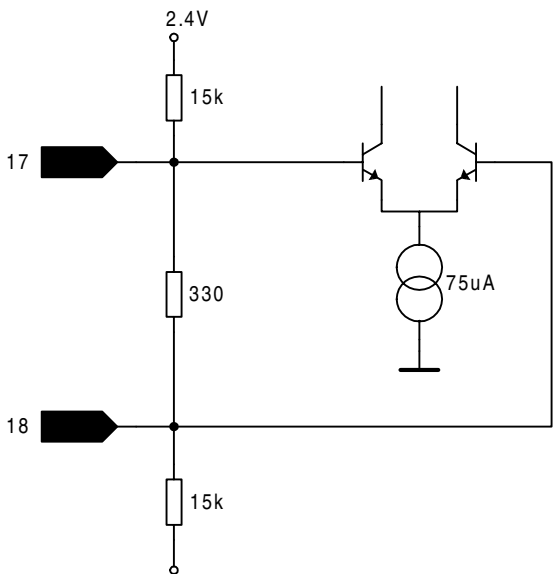
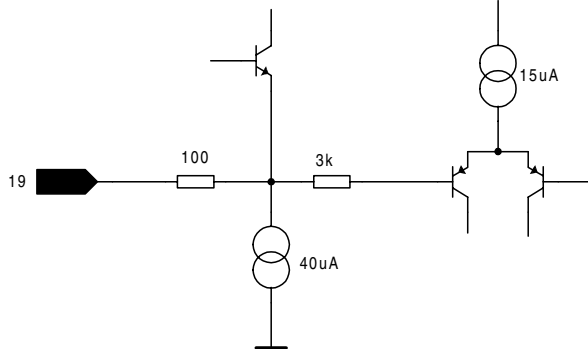
Table 3-1 Pin Definition and Function

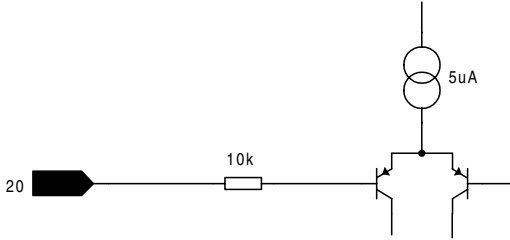
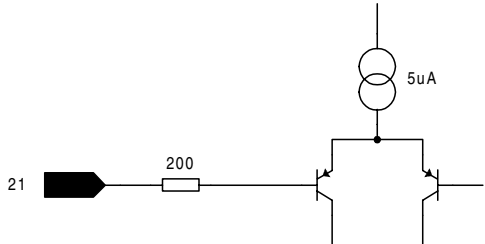
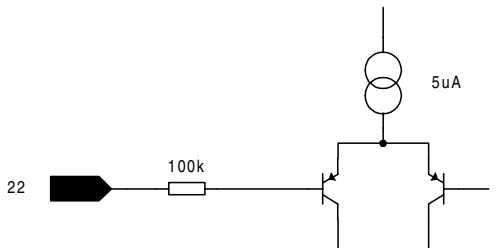
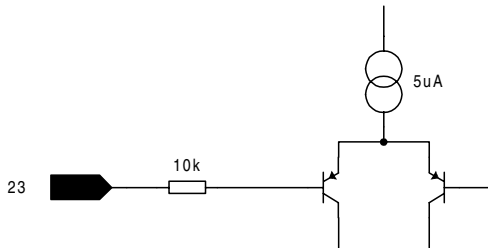
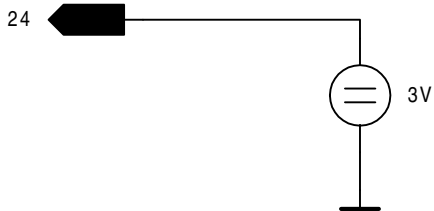
Pin No.	Symbol	Equivalent I/O-Schematic	Function
1	CRST1		External Crystal Connector 1
2	VCC		5V Supply
3	LNI		LNA Input

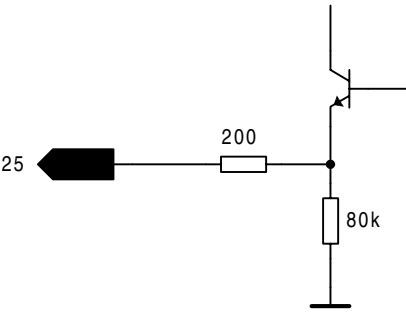
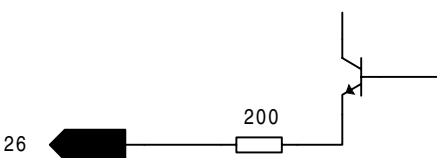
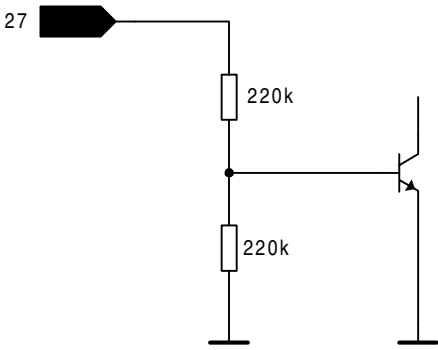
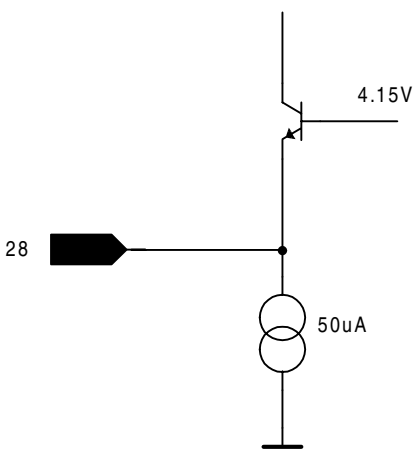
4	TAGC		AGC Time Constant Control
5	AGND		Analogue Ground Return
6	LNO		LNA Output
7	VCC		5V Supply
8	MI		Mixer Input
9	MIX		Complementary Mixer Input
10	AGND		Analogue Ground Return

11	FSEL		869/434 MHz Operating Frequency Selector
12	IFO		10.7 MHz IF Mixer Output
13	DGND		Digital Ground Return
14	VDD		5V Supply (PLL Counter Circuitry)
15	LF		PLL Filter Access Point

Functional Description

16	CSEL		6.xx or 13.xx MHz Quartz Selector
17	LIM		Limiter Input
18	LIMX		Complementary Limiter Input
19	SLP		Data Slicer Positive Input

20	SLN		Data Slicer Negative Input
21	OPP		OpAmp Noninverting Input
22	FFB		Data Filter Feedback Pin
23	THRES		AGC Threshold Input
24	3VOUT		3V Reference Output

25	DATA		Data Output
26	PDO		Peak Detector Output
27	PDWN		Power Down Input
28	CRST2		External Crystal Connector 2

3.3 Functional Block Diagram

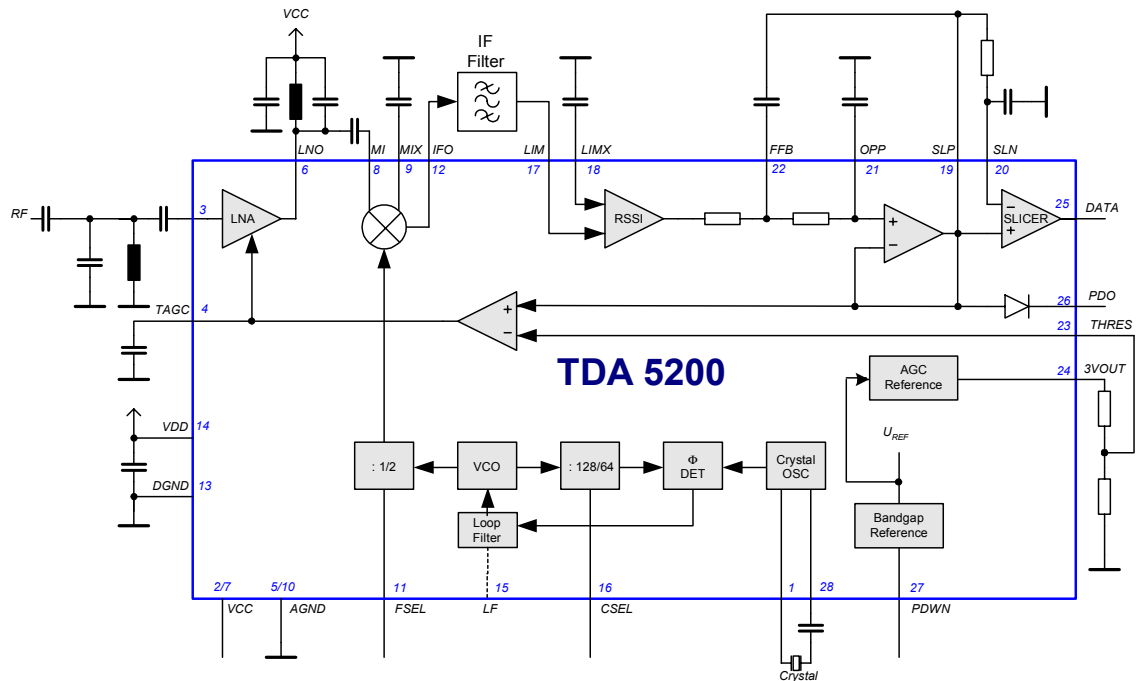


Figure 3-2 Main Block Diagram

3.4 Functional Blocks

3.4.1 Low Noise Amplifier (LNA)

The LNA is an on-chip cascode amplifier with a voltage gain of 15 to 20dB. The gain figure is determined by the external matching networks situated ahead of LNA and between the LNA output **LNO** (Pin 6) and the Mixer Inputs **MI** and **MIX** (Pins 8 and 9). The noise figure of the LNA is approximately 3.2dB, the current consumption is 500µA. The gain can be reduced by approximately 18dB. The switching point of this AGC action can be determined externally by applying a threshold voltage at the **THRES** pin (Pin 23). This voltage is compared internally with the received signal (RSSI) level generated by the limiter circuitry. In case that the RSSI level is higher than the threshold voltage the LNA gain is reduced and vice versa. The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin as described in Section 4.1. The time constant of the AGC action can be determined by connecting a capacitor to the **TAGC** pin (Pin 4) and should be chosen along with the appropriate threshold voltage according to the intended operating case and interference scenario to be expected during operation. The optimum choice of AGC time constant and the threshold voltage is described in Section 4.1.

3.4.2 Mixer

The Double Balanced Mixer downconverts the input frequency (RF) in the range of 433-435MHz/868-870MHz to the intermediate frequency (IF) at 10.7MHz with a voltage gain of approximately 21dB. A low pass filter with a corner frequency of 20MHz is built on chip in order to suppress RF signals to appear at the IF output (**IFO** pin). The IF output is internally consisting of an emitter follower that has a source impedance of approximately 330 Ω to facilitate interfacing the pin directly to a standard 10.7MHz ceramic filter without additional matching circuitry.

3.4.3 PLL Synthesizer

The Phase Locked Loop synthesiser consists of a VCO, an asynchronous divider chain, a phase detector with charge pump and a loop filter and is fully implemented on-chip. The VCO is including spiral inductors and varactor diodes. It's nominal centre frequency is 852MHz. No additional components are necessary. The oscillator signal is fed both to the synthesiser divider chain and to the downconverting mixer. In case of operation in the 433 - 435 MHz range, the signal is divided by two before it is fed to the mixer. This is controlled by the selection pin **FSEL** (Pin 11) as described in the following table. The overall divi-

sion ratio of the divider chain can be selected to be either 128 or 64, depending on the frequency of the reference oscillator quartz (see below). The loop filter is also realised fully on-chip.

Table 3-2 FSEL pin operating states

FSEL	RF Frequency
Open	433 - 435 MHz
Shorted to ground	868 - 870 MHz

3.4.4 Crystal Oscillator

The on-chip crystal oscillator circuitry allows for utilisation of quartzes both in the 6 and 13MHz range as the overall division ratio of the PLL can be switched between 64 and 128 via the **CSEL** (Pin 16) pin according to the following table.

Table 3-3 CSEL pin operating states

CSEL	Crystal Frequency
Open	6.xx MHz
Shorted to ground	13.xx MHz

The calculation of the value of the necessary quartz load capacitance is shown in Section 4.3, the quartz frequency calculation is explained in Section 4.4.

3.4.5 Limiter

The Limiter is an AC coupled multistage amplifier with a cumulative gain of approximately 80dB that has a bandpass-characteristic centred around 10.7MHz. It has an input impedance of 330 Ω to allow for easy interfacing to a 10.7MHz ceramic IF filter. The limiter circuit acts as a Receive Signal Strength Indicator (RSSI) generator which produces a DC voltage that is directly proportional to the input signal level as can be seen in Figure 4-2. This signal is used to demodulate the ASK receive signal in the subsequent baseband circuitry and to turn down the LNA gain by approximately 17dB in case the input signal strength is too strong as described in Section 3.4.1 and Section 4.1.

3.4.6 Data Filter

The data filter comprises an OP-Amp with a bandwidth of 100kHz used as a voltage follower and two 100k Ω on-chip resistors. Along with two external capacitors a 2nd order Sallen-Key low pass filter is formed. The selection of the capacitor values is described in Section 4.2.

3.4.7 Data Slicer

The data slicer is a fast comparator with a bandwidth of 100 kHz. This allows for a maximum receive data rate of approximately 120kBaud. The maximum achievable data rate also depends on the IF Filter bandwidth and the local oscillator tolerance values. Both inputs are accessible. The output delivers a digital data signal (CMOS-like levels) for the detector. The self-adjusting threshold on pin 20 is generated by RC-term or peak detector depending on the baseband coding scheme. The data slicer threshold generation alternatives are described in more detail in Section 4.5.

3.4.8 Peak Detector

The peak detector generates a DC voltage which is proportional to the peak value of the receive data signal. An external RC network is necessary. The output can be used as an indicator for the signal strength and also as a reference for the data slicer. The maximum output current is 500µA.

3.4.9 Bandgap Reference Circuitry

A Bandgap Reference Circuit provides a temperature stable reference voltage for the device. A power down mode is available to switch off all subcircuits which is controlled by the PWDN pin (Pin 27) as shown in the following table. The supply current drawn in this case is typically 50nA. .

Table 3-4 PWDN pin operating states	
PWDN	Operating State
Open or tied to ground	Powerdown Mode
Tied to Vs	Receiver On

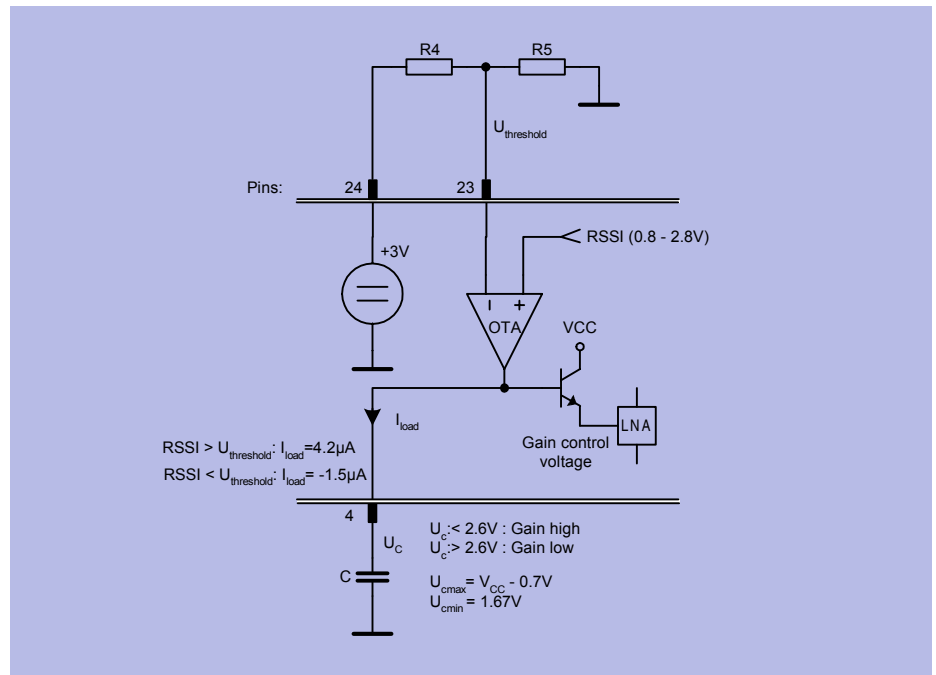
4 Applications

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4.3	Quartz Load Capacitance Calculation	4-5
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4.1 Choice of LNA Threshold Voltage and Time Constant

In the following figure the internal circuitry of the LNA automatic gain control is shown.

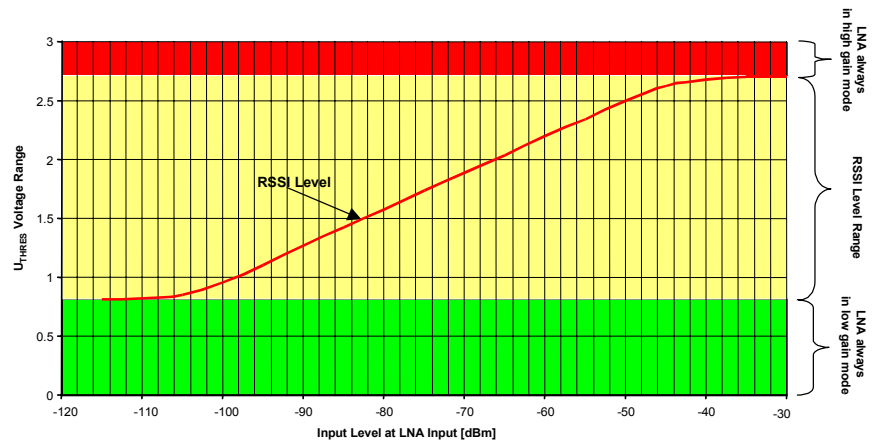


LNA_autom.wmf

Figure 4-1 LNA Automatic Gain Control Circuitry

The LNA automatic gain control circuitry consists of an operational transimpedance amplifier that is used to compare the received signal strength signal (RSSI) generated by the Limiter with an externally provided threshold voltage U_{thres} . As shown in the following figure the threshold voltage can have any value between approximately 0.8 and 2.8V to provide a switching point within the receive signal dynamic range.

This voltage U_{thres} is applied to the **THRES** pin (Pin 23) The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin. If the RSSI level generated by the Limiter is higher than U_{thres} , the OTA generates a positive current I_{load} . This yields a voltage rise on the **TAGC** pin (Pin 4). Otherwise, the OTA generates a negative current. These currents do not have the same values in order to achieve a fast-attack and slow-release action of the AGC and are used to charge an external capacitor which finally generates the LNA gain control voltage.



RSSI-AGC.wmf

Figure 4-2 RSSI Level and Permissive AGC Threshold Levels

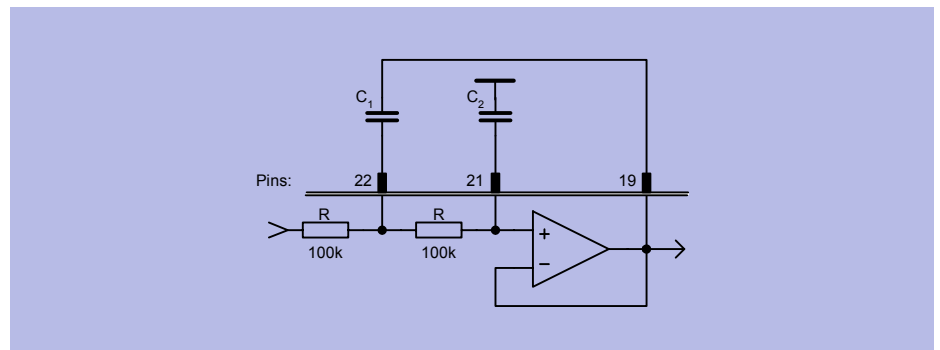
The switching point should be chosen according to the intended operating scenario. The determination of the optimum point is described in the accompanying Application Note, a threshold voltage level of 1.8V is apparently a viable choice. It should be noted that the output of the 3VOUT pin is capable of driving up to 50 μ A, but that the THRES pin input current is only in the region of 40nA. As the current drawn out of the 3VOUT pin is directly related to the receiver power consumption, the power divider resistors should have high impedance values. R4 can be chosen as 120k Ω , R5 as 180k Ω to yield an overall 3VOUT output current of 10 μ A.

Note: If the LNA gain shall be kept in either high or low gain mode this has to be accomplished by tying the **THRES** pin to a fixed voltage. In order to achieve high gain mode operation, a voltage higher than 2.8V shall be applied to the **THRES** pin, such as a short to the **3VOLT** pin. In order to achieve low gain mode operation a voltage lower than 0.7V shall be applied to the **THRES**, such as a short to ground.

As stated above the capacitor connected to the **TAGC** pin is generating the gain control voltage of the LNA due to the charging and discharging currents of the OTA and thus is also responsible for the AGC time constant. As the charging and discharging currents are not equal two different time constants will result. The time constant corresponding to the charging process of the capacitor shall be chosen according to the data rate. According to measurements performed at Infineon the capacitor value should be greater than 47nF.

4.2 Data Filter Design

Utilising the on-board voltage follower and the two 100kΩ on-chip resistors a 2nd order Sallen-Key low pass data filter can be constructed by adding 2 external capacitors between pins 19 (SLP) and 22 (FFB) and to pin 21 (OPP) as depicted in the following figure and described in the following formulas¹.



Filter_Design.wmf

Figure 4-3 Data Filter Design

(1)

$$C_1 = \frac{2Q\sqrt{b}}{R2\pi f_{3dB}}$$

(2)

$$C_2 = \frac{\sqrt{b}}{4QR\pi f_{3dB}}$$

with

$$Q = \frac{\sqrt{b}}{a}$$

(3) the quality factor of the poles

where

in case of a Bessel filter

$$a = 1.3617, b = 0.618$$

and thus

$$Q = 0.577$$

and in case of a Butterworth filter

$$a = 1.141, b = 1$$

and thus

$$Q = 0.71$$

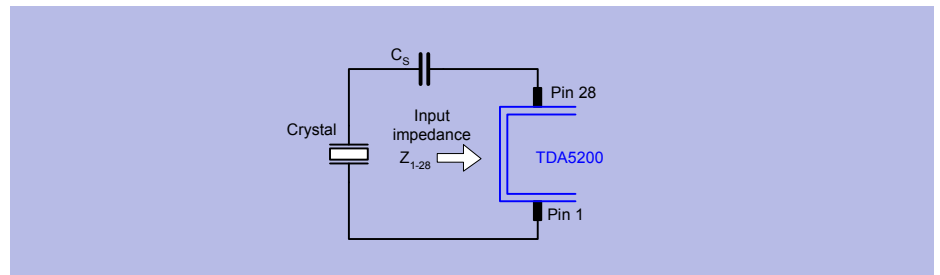
Example: Butterworth filter with $f_{3dB} = 5\text{kHz}$ and $R = 100\text{k}\Omega$:

$$C_1 = 450\text{pF}, C_2 = 225\text{pF}$$

1. taken from Tietze/Schenk: Halbleiterschaltungstechnik, Springer Berlin, 1999

4.3 Quartz Load Capacitance Calculation

The value of the capacitor necessary to achieve that the quartz oscillator is operating at the intended frequency is determined by the reactive part of the negative resistance of the oscillator circuit as shown in Section 5.1.3 and by the quartz specifications given by the quartz manufacturer.



Quartz_load.wmf

Figure 4-4 Determination of Series Capacitance Value for the Quartz Oscillator

Crystal specified with load capacitance

$$C_s = \frac{1}{\frac{1}{C_l} + 2\pi f X_L}$$

with C_l the load capacitance (refer to the quartz crystal specification).

Examples:

6.7 MHz:	$C_L = 12 \text{ pF}$	$X_L = 750 \Omega$	$C_S = 8.7 \text{ pF}$
13.401 MHz:	$C_L = 12 \text{ pF}$	$X_L = 1250 \Omega$	$C_S = 5.3 \text{ pF}$

These values may be obtained in high accuracy by putting two capacitors in series to the quartz, such as 20pF and 15pF in the 6.7MHz case and 15pF and 8.2pF in the 13.401MHz case.

4.4 Quartz Frequency Calculation

The quartz frequency is calculated by using the following formula:

$$f_{QU} = (f_{RF} \pm 10.7) / r \quad (1),$$

with

- f_{RF} receive frequency
- f_{LO} local oscillator (PLL) frequency ($f_{RF} \pm 10.7$)
- f_{QU} quartz oscillator frequency
- r ratio of local oscillator (PLL) frequency and quartz frequency as shown in the subsequent table.

Table 4-1 PLL Division Ratio Dependence on States of FSEL and CSEL		
FSEL	CSEL	Ratio $r = (f_{LO}/f_{QU})$
open	open	64
open	GND	32
GND	open	128
GND	GND	64

Subtraction of 10.7 occurs in case the receive frequency is higher than the intended local oscillator frequency, addition in case the receive frequency lies below the local oscillator frequency.

Examples:

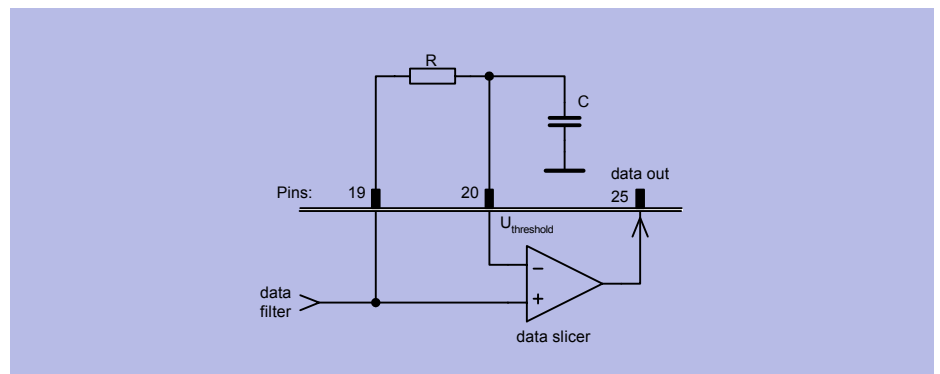
$$f_{QU} = (868.4MHz - 10.7MHz) / 64 = 13.40156MHz$$

$$f_{QU} = (868.4MHz - 10.7MHz) / 128 = 6.7008MHz$$

$$f_{QU} = (434.2MHz - 10.7MHz) / 32 = 13.23437MHz$$

4.5 Data Slicer Threshold Generation

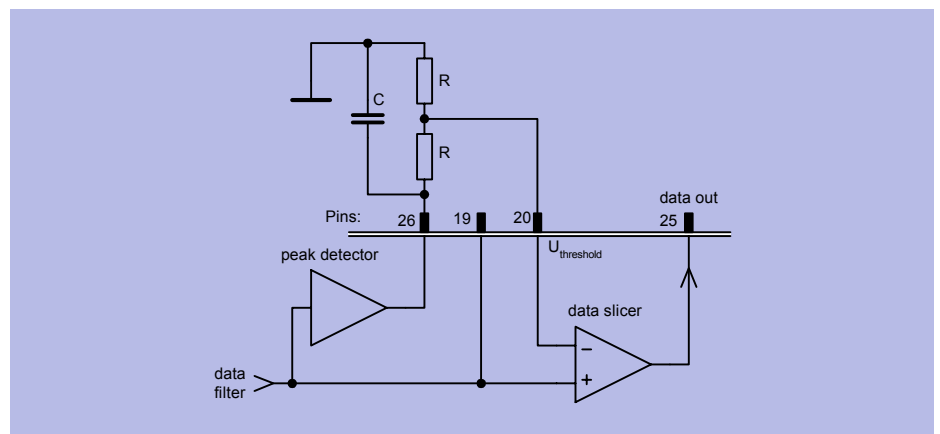
The threshold of the data slicer can be generated in two ways, depending on the signal coding scheme used. In case of a signal coding scheme without DC content such as Manchester coding the threshold can be generated using an external R-C integrator as shown in the following . The cut-off frequency of the R-C integrator has to be lower than the lowest frequency appearing in the data signal. In order to keep distortion low, the minimum value for R is 20k Ω .



Data_slice1.wmf

Figure 4-5 Data Slicer Threshold Generation with External R-C Integrator

Another possibility for threshold generation is to use the peak detector in connection with two resistors and one capacitor as shown in the following figure. The component values are depending on the coding scheme and the protocol used.



Data_slice2.wmf

Figure 4-6 Data Slicer Threshold Generation Utilising the Peak Detector

5

Reference

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5.3	Test Board Layouts.	5-10
5.4	Bill of Materials	5-12

5.1 Electrical Data

5.1.1 Absolute Maximum Ratings



WARNING

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

Table 5-1 Absolute Maximum Ratings, Ambient temperature $T_{AMB} = -40^{\circ}\text{C} \dots +85^{\circ}\text{C}$

#	Parameter	Symbol	Limit Values		Unit	Remarks
			min	max		
1	Supply Voltage	V_s	-0.3	5.5	V	
2	Junction Temperature	T_j	-40	+150	$^{\circ}\text{C}$	
3	Storage Temperature	T_s	-40	+125	$^{\circ}\text{C}$	
4	Thermal Resistance	R_{thJA}		114	K/W	
5	ESD integrity, all pins	V_{ESD}	-1	+1	kV	HBM according to MIL STD 883D, method 3015.7

5.1.2 Operating Range

Within the operating range the IC operates as explained in the circuit description. The AC/DC characteristic limits are not guaranteed.

Supply voltage: VCC = 4.5V .. 5.5V

Table 5-2 Operating Range, Ambient temperature $T_{AMB} = -40^{\circ}\text{C} \dots +85^{\circ}\text{C}$

#	Parameter	Symbol	Limit Values		Unit	Test Conditions	L	Item
			min	max				
1	Supply Current	$I_{S\ 868}$ $I_{S\ 434}$		5.6 5.4	mA mA	$f_{RF} = 868\text{MHz}$ $f_{RF} = 434\text{MHz}$		
2	Receiver Input Level	RF_{in}	-107	-13	dBm	@ source impedance 50Ω, BER 2E-3, average power level, Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	■	
3	LNI Input Frequency	f_{RF}	433/ 868	435/ 870	MHz			
4	MI/X Input Frequency	f_{MI}	433/ 868	435/ 870	MHz			
5	3dB IF Frequency Range	$f_{IF\ -3dB}$	5	23	MHz			
6	Powerdown Mode On	$PWDN_{ON}$	0	0.8	V			
7	Powerdown Mode Off	$PWDN_{OFF}$	2	V_S	V			
8	Gain Control Voltage, LNA high gain state	V_{THRES}	2.8	V_S	V			
9	Gain Control Voltage, LNA low gain state	V_{THRES}	0	0.7V	V			

■ This value is guaranteed by design.

5.1.3 AC/DC Characteristics

AC/DC characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production. The device performance parameters marked with ■ were measured on an Infineon evaluation board as described in Section 5.2..

Table 5-3 AC/DC Characteristics with T_A 25 °C, $V_{CC} = 4.5 \dots 5.5$ V

#	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item
			min	typ	max				

Supply

Supply Current

1	Supply current, standby mode	$I_{S\ PDWN}$		50	70	nA	Pin 27 (PDWN) open or tied to 0 V		
2	Supply current, device operating at 868MHz	$I_{S\ 868}$		4.8	5.2	mA	Pin 11 (FSEL) tied to GND		
3	Supply current, device operating at 434 MHz	$I_{S\ 434}$		4.6	5	mA	Pin 11 (FSEL) open		

LNA

Signal Input LNI (PIN 3), $V_{THRES} > 2.8V$, high gain mode

1	Average Power Level at BER = 2E-3 (Sensitivity)	RF_{in}		-110		dBm	Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	■	
2	Input impedance, $f_{RF}=434$ MHz	$S_{11\ LNA}$	0.873 / -34.7 deg					■	
3	Input impedance, $f_{RF}=869$ MHz	$S_{11\ LNA}$	0.738 / -73.5 deg					■	
4	Input level @ 1dB compression	$P1dB_{LNA}$		-15		dBm		■	
5	Input 3 rd order intercept point $f_{RF}=434$ MHz	$IIP3_{LNA}$		-10		dBm	matched input	■	
6	Input 3 rd order intercept point $f_{RF}=869$ MHz	$IIP3_{LNA}$		-14		dBm	matched input	■	
7	LO signal feedthrough at antenna port	LO_{LNI}			-73	dBm		■	

Signal Output LNO (PIN 6), $V_{THRES} > 2.8V$, high gain mode

1	Gain $f_{RF}=434$ MHz	$S_{21\ LNA}$	1.509 / 138.2 deg					■	
2	Gain $f_{RF}=869$ MHz	$S_{21\ LNA}$	1.419 / 101.7 deg					■	
3	Output impedance, $f_{RF}=434$ MHz	$S_{22\ LNA}$	0.886 / -12.9 deg					■	

Table 5-3 AC/DC Characteristics with T_A 25 °C, $V_{CC} = 4.5 \dots 5.5$ V (continued)

	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item
			min	typ	max				
4	Output impedance, $f_{RF}=869$ MHz	S_{22} LNA	0.866 / -24.2 deg					■	
5	Voltage Gain Antenna to MI $f_{RF}=434$ MHz	G_{AntMI}		42		dB			
6	Voltage Gain Antenna to MI $f_{RF}=869$ MHz	G_{AntMI}		40		dB			
7	Noise Figure	NF_{LNA}		t.b.d.		dB		■	

Signal Input LNI, $V_{THRES} = GND$, low gain mode

1	Input impedance, $f_{RF}=434$ MHz	S_{11} LNA	0.873 / -34.7 deg					■	
2	Input impedance, $f_{RF}=869$ MHz	S_{11} LNA	0.738 / -73.5 deg					■	
3	Input level @ 1dB C. P $f_{RF} = 434$ MHz	$P1dB_{LNA}$		-18		dBm	matched input	■	
4	Input level @ 1dB C. P $f_{RF} = 869$ MHz	$P1dB_{LNA}$		-6		dBm	matched input	■	
5	Input 3 rd order intercept point $f_{RF}=434$ MHz	$IIP3_{LNA}$		-10		dBm	matched input	■	
6	Input 3 rd order intercept point $f_{RF}=869$ MHz	$IIP3_{LNA}$		-5		dBm	matched input	■	

Signal Output LNO, $V_{THRES} = GND$, low gain mode

1	Gain $f_{RF}=434$ MHz	S_{21} LNA	0.183 / 140.6 deg					■	
2	Gain $f_{RF}=869$ MHz	S_{21} LNA	0.179 / 109.1deg					■	
3	Output impedance, $f_{RF}=434$ MHz	S_{22} LNA	0.897 / -13.6 deg					■	
4	Output impedance, $f_{RF}=869$ MHz	S_{22} LNA	0.868 / -26.3 deg					■	
5	Voltage Gain Antenna to MI $f_{RF}=434$ MHz	G_{AntMI}		22		dB			
6	Voltage Gain Antenna to MI $f_{RF}=869$ MHz	G_{AntMI}		19		dB			
7	Noise Figure	NF_{LNA}		t.b.d.		dB		■	

Signal 3VOUT (PIN 24)

1	Output voltage	V_{3VOUT}		3		V			
2	Current out	I_{3VOUT}			50	μA			

Signal THRES (PIN 23)

1	Input Voltage range	V_{THRES}	0		V_S-1V	V	see Section 4.1		
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Table 5-3 AC/DC Characteristics with T_A 25 °C, $V_{CC} = 4.5 \dots 5.5$ V (continued)

	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item
			min	typ	max				
2	LNA low gain mode	V_{THRES}	0			V			
3	LNA high gain mode	V_{THRES}	2.8	3	V_S	V	or shorted to Pin 24		
4	Current in	I_{THRES_in}		5		nA			

Signal TAGC (PIN 4)

1	Current out, LNA low gain state	I_{TAGC_out}		4.2		μA	$RSSI > V_{THRES}$		
2	Current in, LNA high gain state	I_{TAGC_in}		1.5		μA	$RSSI < V_{THRES}$		

MIXER
Signal Input MI/MIX (PINS 8/9)

1	Input impedance, $f_{RF}=434$ MHz	$S_{11\ MIX}$	0.942 / -14.4 deg					■	
2	Input impedance, $f_{RF}=869$ MHz	$S_{11\ MIX}$	0.918 / -28.1 deg					■	
3	Input 3 rd order intercept point $f_{RF}=434$ MHz	$IIP3_{MIX}$		-28		dBm		■	
4	Input 3 rd order intercept point $f_{RF}=869$ MHz	$IIP3_{MIX}$		-26		dBm		■	

Signal Output IFO (PIN 12)

1	Output impedance	Z_{IFO}		330		Ω			
2	Conversion Voltage Gain $f_{RF}=434$ MHz	G_{MIX}		+19		dB			
3	Conversion Voltage Gain $f_{RF}=869$ MHz	G_{MIX}		+18		dB			
4	Noise Figure, SSB (~DSB NF+3dB)	NF_{MIX}		t.b.d.		dB		■	
5	RF to IF isolation	A_{RF-IF}		t.b.d.		dB		■	

LIMITER
Signal Input LIM/X (PINS 17/18)

1	Input Impedance	Z_{LIM}	264	330	396	Ω		■	
2	RSSI dynamic range	DR_{RSSI}	60		80	dB			
3	RSSI linearity	LIN_{RSSI}		± 1		dB		■	
4	Operating frequency (3dB points)	f_{LIM}	5	10.7	23	MHz		■	

Table 5-3 AC/DC Characteristics with T_A 25 °C, $V_{CC} = 4.5 \dots 5.5$ V (continued)

	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item
			min	typ	max				

DATA FILTER

1	Useable bandwidth	BW_{BB} FILT			100	kHz		■	
2	RSSI Level at Data Filter Output SLP	$RSSI_{low}$	0.9			V	LNA in high gain $RF_{IN}=-103dBm$		
3	RSSI Level at Data Filter Output SLP	$RSSI_{high}$			2.8	V	LNA in high gain. $RF_{IN}=-30dBm$		

SLICER

Signal Output DATA (PIN 25)

1	Useable bandwidth	BW_{BB} SLIC			100	kHz		■	
2	Capacitive loading of output	C_{max} SLIC			20	pF			
3	LOW output voltage	V_{SLIC_L}		0		V			
4	HIGH output voltage	V_{SLIC_H}			V_S-1V	V			
5	Output current	I_{SLIC_out}			200	μA			

PEAK DETECTOR

Signal Output PDO (PIN 26)

1	LOW output voltage	V_{SLIC_L}		0		V			
2	HIGH output voltage	V_{SLIC_H}			V_S-1	V			
3	Load current	I_{load}			500	μA			
4	Leakage current	$I_{leakage}$		700		nA			

CRYSTAL OSCILLATOR

Signals CRSTL1, CRISTL 2, (PINS 1/28)

1	Operating frequency	f_{CRSTL}	6		14	MHz	fundamental mode, series resonance		
2	Input Impedance @ ~6MHz	Z_{1-28}		-900 +j750		Ω		■	
3	Input Impedance @ ~13MHz	Z_{1-28}		-450 +j1250		Ω		■	
4	Serial Capacity @ ~6MHz	$C_{S6}=C1$		8.7		pF			
5	Serial Capacity @ ~13MHz	$C_{S13}=C1$		5.3		pF			

Table 5-3 AC/DC Characteristics with T_A 25 °C, $V_{CC} = 4.5 \dots 5.5$ V (continued)

	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item
			min	typ	max				
PLL									
Signal LF (PIN 15)									
1	Tuning voltage relative to V_s	V_{TUNE}	0.4	1.6	2.4	V			
POWER DOWN MODE									
Signal PDWN (PIN 27)									
1	Powerdown Mode On	$PWDN_{ON}$	0		0.8	V			
2	Powerdown Mode Off	$PWDN_{Off}$	2.8		V_S	V			
3	Input bias current PDWN	I_{PDWN}		t.b.d.		μA			
4	Start-up Time until valid IF signal is detected	T_{SU}			1	ms			
VCO MULTIPLEXER									
Signal FSEL (PIN 11)									
1	f_{RF} range 434 MHz	V_{FSEL}	1.4		4	V	or open		
2	f_{RF} range 869 MHz	V_{FSEL}	0		0.2	V			
3	Input bias current FSEL	I_{FSEL}		200		μA	FSEL tied to GND		
PLL DIVIDER									
Signal CSEL (PIN 16)									
1	f_{CRSTL} range 6.xxMHz	V_{CSEL}	1.4		4	V	or open		
2	f_{CRSTL} range 13.xxMHz	V_{CSEL}	0		0.2	V			
3	Input bias current CSEL	I_{CSEL}		5		μA	CSEL tied to GND		

■ Measured only in lab.

5.2 Test Circuit

The device performance parameters marked with ■ in Section 5.1.3 were measured on an Infineon evaluation board. This evaluation board can be obtained together with evaluation boards of the accompanying transmitter device TDA5100 in an evaluation kit that may be ordered on the INFINEON RKE Webpage www.infineon.com/rke

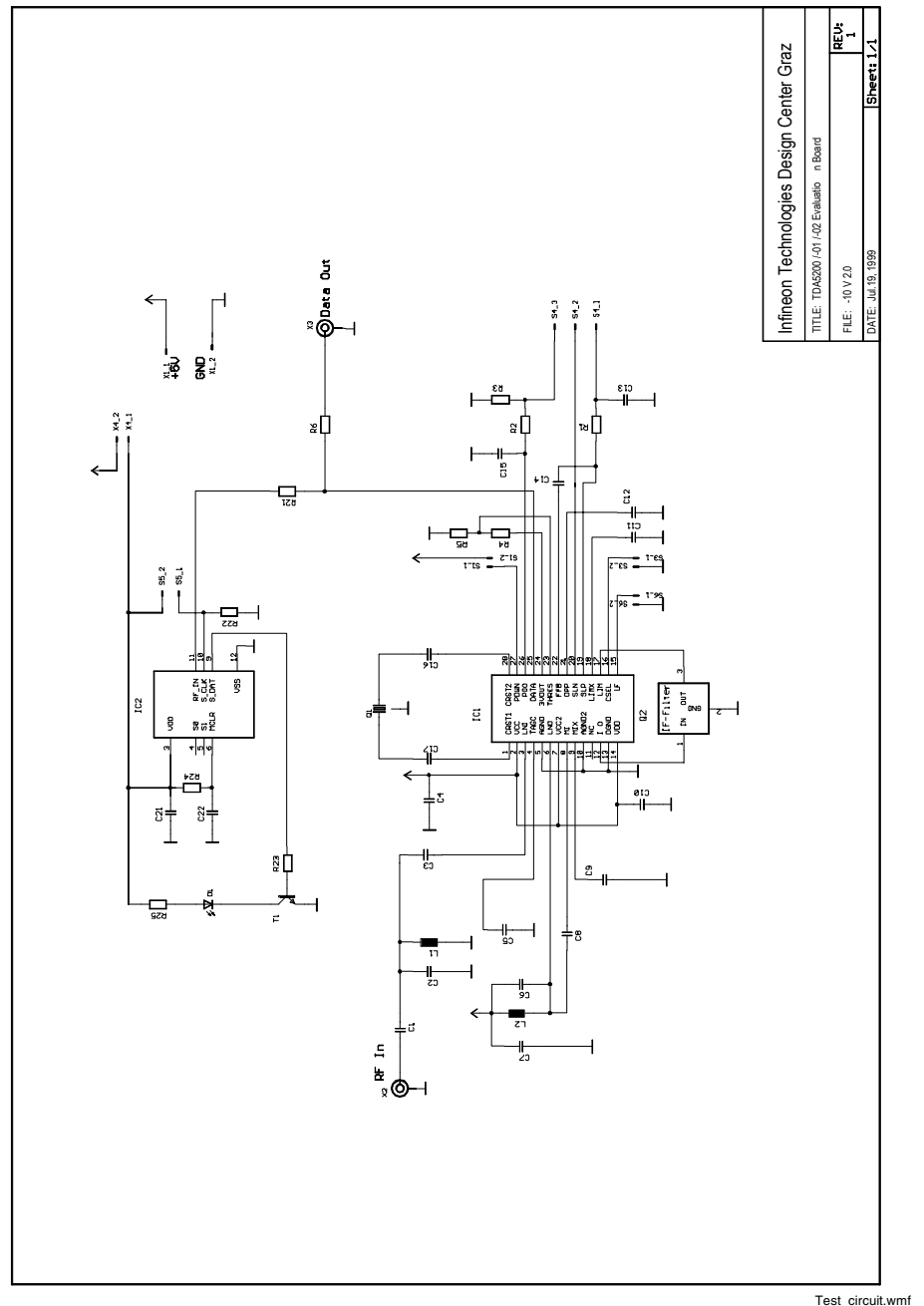


Figure 5-1 Schematic of the Evaluation Board

5.3 Test Board Layouts

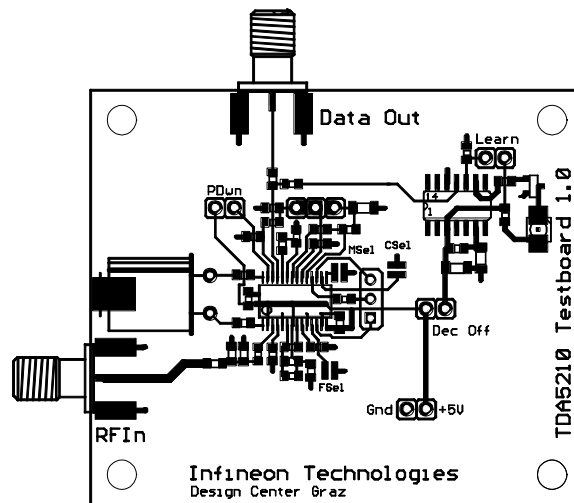


Figure 5-2 Top Side of the Evaluation Board

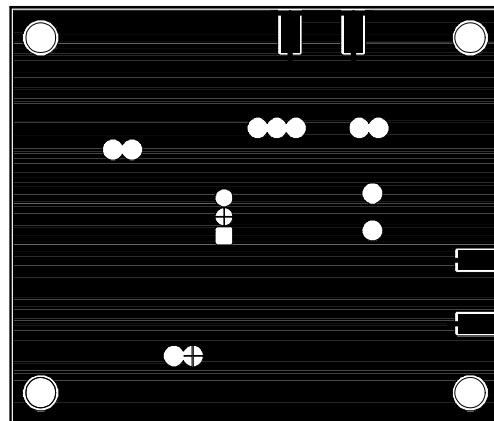


Figure 5-3 Bottom Side of the Evaluation Board

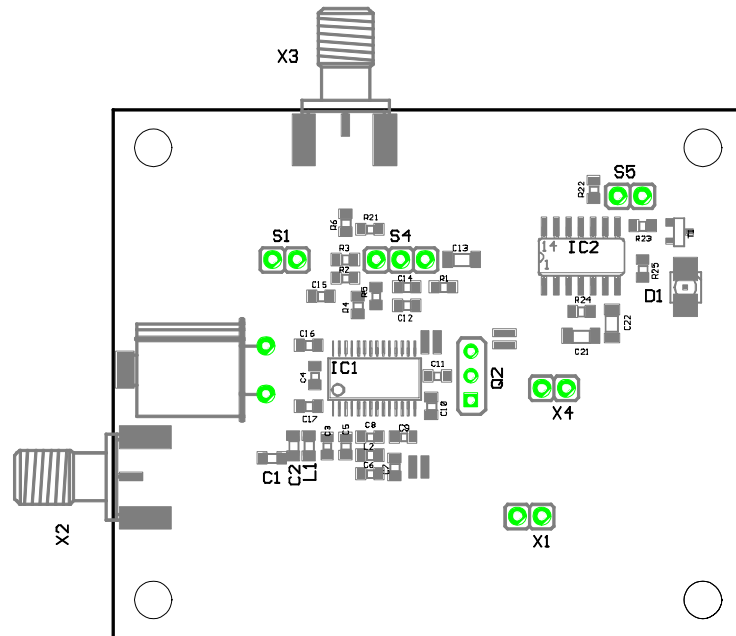


Figure 5-4 Component Placement on the Evaluation Board

5.4 Bill of Materials

The following components are necessary for evaluation of the TDA5200 without use of a Microchip HCS515 decoder.

Table 5-4 Bill of Materials

Ref	Value	Specification
R1	100k Ω	0805, $\pm 5\%$
R2	100k Ω	0805, $\pm 5\%$
R3	820k Ω	0805, $\pm 5\%$
R4	120k Ω	0805, $\pm 5\%$
R5	180k Ω	0805, $\pm 5\%$
R6	10k Ω	0805, $\pm 5\%$
L1	434 MHz: 15nH 869 MHz: 3.3nH	Toko, PTL2012-F15N0G Toko, PTL2012-F3N3C
L2	434 MHz: 8.2pF 869 MHz: 3.9nH	0805, COG, $\pm 0.1\text{pF}$ Toko, PTL2012-F3N9C
C1	1pF	0805, COG, $\pm 0.1\text{pF}$
C2	434 MHz: 4.7pF 869 MHz: 3.9pF	0805, COG, $\pm 0.1\text{pF}$ 0805, COG, $\pm 0.1\text{pF}$
C3	434 MHz: 6.8pF 869 MHz: 5.6pF	0805, COG, $\pm 0.1\text{pF}$ 0805, COG, $\pm 0.1\text{pF}$
C4	100pF	0805, COG, $\pm 5\%$
C5	47nF	1206, X7R, $\pm 10\%$
C6	434 MHz: 10nH 869 MHz: 3.9pF	Toko, PTL2012-F10N0G 0805, COG, $\pm 0.1\text{pF}$
C7	100pF	0805, COG, $\pm 5\%$
C8	434 MHz: 33pF 869 MHz: 22pF	0805, COG, $\pm 5\%$ 0805, COG, $\pm 5\%$
C9	100pF	0805, COG, $\pm 5\%$
C10	10nF	0805, X7R, $\pm 10\%$
C11	10nF	0805, X7R, $\pm 10\%$
C12	220pF	0805, COG, $\pm 5\%$
C13	47nF	0805, X7R, $\pm 10\%$
C14	470pF	0805, COG, $\pm 5\%$
C15	47nF	0805, X7R, $\pm 5\%$
C16	15pF	0805, COG, $\pm 1\%$
C17	8.2pF	0805, COG, $\pm 1\%$
Q2	$(f_{\text{RF}} - 10.7\text{MHz})/32$ or $(f_{\text{RF}} - 10.7\text{MHz})/64$	HC49/U, fundamental mode, CL = 12pF, e.g. 434.2MHz: Jauch Q 13,23437-S11-1323-12-10/20 e.g. 868.4MHz: Jauch Q 13,40155-S11-1323-12-10/20

Table 5-4 Bill of materials (continued)

Ref	Value	Specification
F1	SFE10.7MA5-A or SKM107M1-A20-10	Murata Toko
X2, X3	142-0701-801	Johnson
X1, X4, S1, S5		2-pole pin connector
S4		3-pole pin connector, or not equipped
IC1	TDA 5200	Infineon

Please note that in case of operation at 434 MHz a capacitor has to be soldered in place of L2 and an inductor in place of C6.

The following components are necessary in addition to the above mentioned ones for evaluation of the TDA5200 in conjunction with a Microchip HCS515 decoder.

Table 5-5 Bill of Materials Addendum

Ref	Value	Specification
R21	22k Ω	0805, \pm 5%
R22	100k Ω	0805, \pm 5%
R23	22k Ω	0805, \pm 5%
R24	820k Ω	0805, \pm 5%
R25	560k Ω	0805, \pm 5%
C21	100nF	1206, X7R, \pm 10%
C22	100nF	1206, X7R, \pm 10%
IC2	HCS515	Microchip
T1	BC 847B	Infineon
D1	LS T670-JL	Infineon

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Datasheets for electronic components.